

T835H, T850H

Snubberless™

High temperature 8 A Triacs

Main characteristics

Symbol	Value	Unit
I _{T(RMS)}	8	Α
V _{DRM} /V _{RRM}	600	V
I _{GT}	35 or 50	mA

Features

- Medium current Triac
- 150° C max. T_i turn-off commutation
- Low thermal resistance with clip bonding
- Very high 3 quadrant commutation capability
- Packages are RoHS (2002/95/EC) compliant

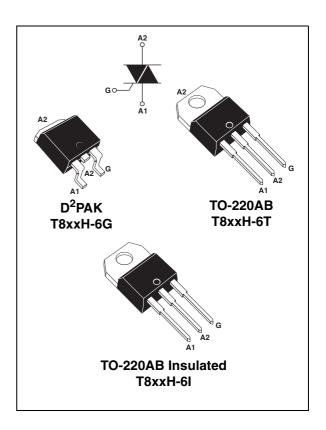
Applications

Especially designed to operate in high power density or universal motor applications such as vacuum cleaner and washing machine drum motor, these 8 A triacs provide a very high switching capability up to junction temperatures of 150° C.

The heatsink can be reduced, compared to traditional triacs, according to the high performance at given junction temperatures.

Description

Available in through-hole or surface mount packages, the T835H and T850H triac series are suitable for general purpose mains power AC switching.



Order codes

Part Numbers	Marking
T835H-6G	T835H 6G
T850H-6G	T850H 6G
T835H-6G-TR	T835H 6G
T850H-6G-TR	T850H 6G
T835H-6T	T835H 6T
T850H-6T	T850H 6T
T835H-6I	T835H 6I
T850H-6I	T850H 6I

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Table 1. Absolute Maximum Ratings

Symbol	Parameter			Value	Unit
	PMS on state current (full sine ways)	D^2 PAK, TO-220AB $T_c = 135^{\circ}$ C		8	Α
IT(RMS)	RMS on-state current (full sine wave)	TO-220AB Ins	T _c = 125° C	0	A
1.	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	80	Α
ITSM	current (full cycle, T _j initial = 25° C)	F = 60 Hz	t = 16.7 ms	84	A
l ² t	I ² t Value for fusing	t _p = 10 ms		42	A ² s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 150° C	50	A/µs
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage	t _p = 10 ms	T _j = 25° C	V _{DRM} /V _{RRM} + 100	V
I _{GM}	teak gate current $t_p = 20 \mu s$ $T_j = 150^{\circ} C$		4	Α	
P _{G(AV)}	Average gate power dissipation $T_j = 150^{\circ} \text{ C}$			1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C

Table 2. Electrical Characteristics ($T_j = 25^{\circ}$ C, unless otherwise specified)

Symbol	Symbol Test Conditions	Quadrant		Value		Unit
Symbol	rest Conditions	Quadrant		T835H	T850H	
I _{GT} ⁽¹⁾	V _D = 12 V R _I = 33 Ω	1 - 11 - 111	MAX.	35	50	mA
V _{GT}	AD = 15 A UE = 22.75	1 - 11 - 111	MAX.	1.0		V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$ I - II - III		MIN.	0.15		V
I _H ⁽²⁾	I _T = 500 mA		MAX.	35	75	mA
1	1 101		MAX.	50	60	mA
ΙL	$I_{G} = 1.2 I_{GT}$	П	IVIAA.	80	110	ША
dV/dt (2)	$V_D = 67\% V_{DRM,}$ gate open, $T_j = 150^{\circ} C$		MIN.	1000	1500	V/µs
(dl/dt)c (2)	Without snubber, T _j = 150° C		MIN.	11	14	A/ms

^{1.} minimum $I_{\mbox{\scriptsize GT}}$ is guaranted at 20% of $I_{\mbox{\scriptsize GT}}$ max.

^{2.} for both polarities of A2 referenced to A1.

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Table 3. Static Characteristics

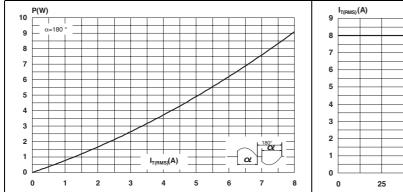
Symbol	Test Conditions			Value	Unit
V _T ⁽¹⁾	I _{TM} = 11 A, t _p = 380 μs	T _j = 25° C	MAX.	1.5	V
V _{t0} (1)	Threshold voltage	T _j = 150° C	MAX.	0.80	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150° C	MAX.	52	mΩ
	$V_{DRM} = V_{RRM}$	T _j = 25° C	MAX.	5	μA
I _{DRM}		T _j = 150° C	MAX.	3.1	
I _{RRM} ⁽²⁾	V _D /V _R = 400 V (at peak mains voltage)	T _j = 150° C	MAX.	2.5	mA
	V _D /V _R = 200 V (at peak mains voltage)	T _j = 150° C	MAX.	2.0	

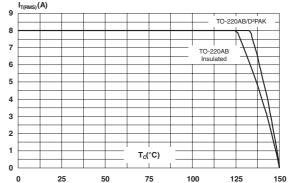
^{1.} for both polarities of A2 referenced to A1.

Table 4. Thermal resistance

Symbol	Parameter			Value	Unit
В	R _{th(j-c)} Junction to case (AC)		D ² PAK / TO-220AB	1.85	
□th(j-c)			TO-220AB Ins	3.7	° C/W
D	Junction to ambient		D ² PAK	45	C/VV
R _{th(j-a)} Junction to ambient		TO-220AB / TO-220AB Ins	60		

Figure 1. Maximum power dissipation versus Figure 2. RMS on-state current versus case RMS on-state current (full cycle) temperature (full cycle)



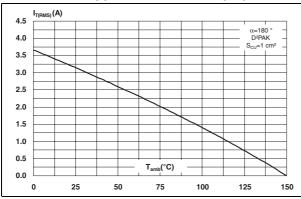


^{2.} $t_p = 380 \ \mu s$.

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Figure 3. RMS on-state current versus ambient temperature (Epoxy printed circuit board FR4, copper thickness = 35 µm)

Figure 4. Variation of thermal impedance versus pulse duration



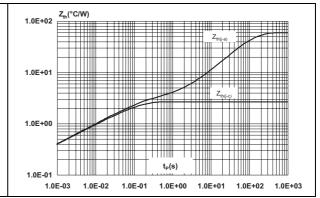
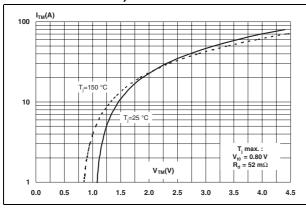


Figure 5. On-state characteristics (maximum Figure 6. values)

Surge peak on-state current versus number of cycles



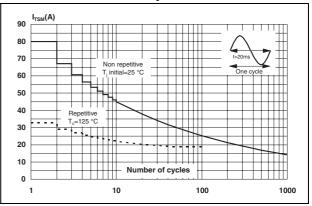
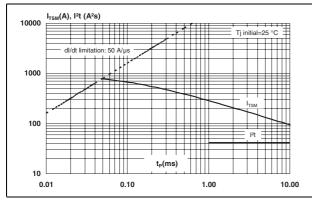
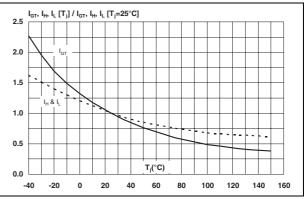


Figure 7. Non-repetitive surge peak on-state Figure 8. current for a sinusoidal pulse with width $t_p < 10 \text{ ms}$ and corresponding value of I^2t

Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

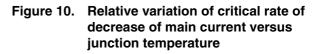


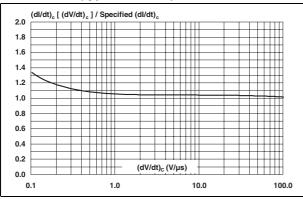


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Figure 9. Relative variation of critical rate of Figure 10. decrease of main current (dl/dt)c versus reapplied (dV/dt)c (typical values)





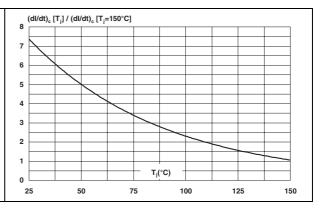
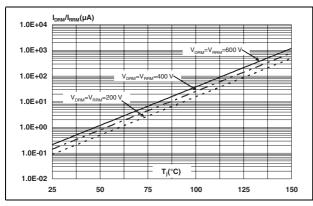
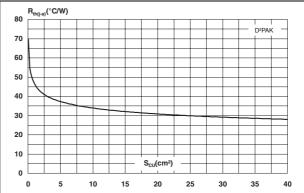


Figure 11. Leakage current versus junction temperature for different values of blocking voltage (typical values)

Figure 12. Variation of thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness = 35 μm)

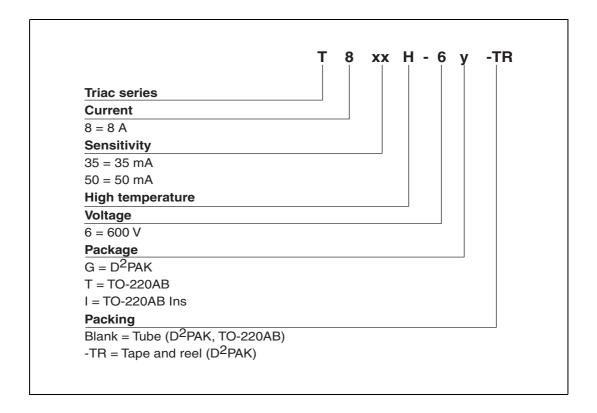




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Ordering information T835H, T850H

2 Ordering information



Inches

Тур.

Max.

0.181

0.106

0.009

0.037

0.024

0.054

0.368

0.405

0.208

0.624

0.055

0.069

8°

0.016

Package mechanical data 3

- Epoxy meets UL94, V0
- Recommended torque 0.4 to 0.6 Nm

D²PAK dimensions Table 5.

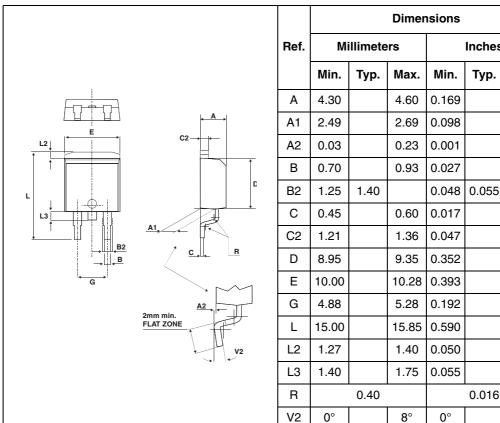
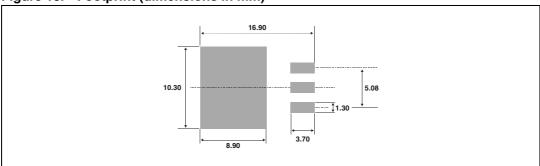


Figure 13. Footprint (dimensions in mm)



Dimensions Millimeters Ref. Inches Min. Typ. Max. Min. Typ. Max. 15.20 15.90 0.598 0.625 0.147 a1 3.75 В 13.00 14.00 0.511 0.551 a2 В 10.40 0.393 10.00 0.409 0.88 0.034 b1 0.61 0.024 b2 1.23 1.32 0.048 0.051 14 С 4.40 4.60 0.173 0.181 0.49 0.70 0.019 0.027 с1 c2 2.40 2.72 0.094 0.107 c2 12 2.40 2.70 0.094 0.106 е F 6.20 0.244 0.259 6.60 ØΙ 3.75 3.85 0.147 0.151 14 15.80 16.40 16.80 0.622 0.646 0.661 L 2.65 2.95 0.104 0.116 12 1.14 0.044 0.066 1.70 13 1.14 1.70 0.044 0.066 Μ 2.60 0.102

Table 6. TO-220AB and TO-220AB Ins dimensions

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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4 Ordering Information

T835H, T850H

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
T8xxH-6G	T8xxH 6G	D ² PAK	1.5 g	50	Tube
T8xxH-6G-TR	T8xxH 6G	D ² PAK	1.5 g	1000	Tape and reel
T8xxH-6T	T8xxH 6T	TO-220AB	2.3 g	50	Tube
T8xxH-6I	T8xxH 6I	TO-220AB Ins	2.3 g	50	Tube

5 Revision history

Date	Revision	Description of Changes
17-Apr-2007	1	First issue

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